

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5056	((substrate wafer) with (chamber reactor)) with (reactant precursor)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 13:32
L2	1397	L1 and (activated irradiated energy) with (reactant precursor)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 13:32
L3	407	L2 and (activated irradiated energy) with (ray infrared microwave)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 13:32
L4	258	L3 and (activated irradiated energy) with (temperature)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 13:32
L5	103	L4 and (activated irradiated energy) with (molecular)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 13:33
L6	103	L4 and (activated irradiated energy) with (molecular)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 13:34
L7	7	(thin adj film and first adj reactant and first adj energy and second adj energy first adj chemisorbed).clm.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/10/28 13:36
L8	6	(thin adj film and first adj reactant and first adj energy and second adj energy first adj chemisorbed).clm.	US-PGPU B	OR	ON	2005/10/28 13:37

☐ Pending

☒ Active

- ☞ L1: (5056) ((substrate wafer) with (chamber reactor)) with (reactant precursor)
- ☞ L2: (1397) L1 and (activat\$4 irradiat\$3 ener\$5) with (reactant precursor)
- ☞ L3: (407) L2 and (activat\$4 irradiat\$3 ener\$5) with (ray infrared microwave)
- ☞ L4: (258) L3 and (activat\$4 irradiat\$3 ener\$5) with (temperature)
- ☞ L5: (103) L4 and (activat\$4 irradiat\$3 ener\$5) with (molecul\$3)
- ☞ L6: (103) L4 and (activat\$4 irradiat\$3 ener\$5) with (molecul\$3)

Search:

DBs: US-PGPUB; USPAT; EPO; JPO ☒ Duplicates ☒ Highlight all hit terms initially

Default operator: GOR

L4 and (activat\$4 irradiat\$3 ener\$5) with (molecul\$3)

☒ BRS form
 ☒ ISAR form
 ☒ Image
 ☒ Text
 ☒ HTML

	U	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	3
1	<input checked="" type="checkbox"/>	US 2005018	2005082		Photo-assisted method fo	438/660	438/584;		Agarwal, Vishnu K.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
2	<input checked="" type="checkbox"/>	US 2005017	2005081		Method for energy-assiste	427/457	427/585		Helms Jr, Aubrey L	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
3	<input checked="" type="checkbox"/>	US 2005015	2005072		Preheating of chemical va	438/680			Derderian, Garo J. e	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
4	<input checked="" type="checkbox"/>	US 2005013	2005061		Apparatus and methods f	623/1.42			Sirhan, Motasim et	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
5	<input checked="" type="checkbox"/>	US 2005011	2005060	11	Deposition of fluorosilse	257/758	257/760;		Hacker, Nigel P.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
6	<input checked="" type="checkbox"/>	US 2005010	2005051	58	Apparatus and methods f	623/1.42			Sirhan, Motasim et	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
7	<input checked="" type="checkbox"/>	US 2005007	2005033	39	Post-deposition treatment	438/789	257/E21.2		Xia, Li-Qun et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
8	<input checked="" type="checkbox"/>	US 2005003	2005021	20	Methods for forming a thi	438/689			Ko, Chang-Hyun et	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
9	<input checked="" type="checkbox"/>	US 2005000	2005010	31	Reactor for producing rea	118/715	257/E21.2		Lee, Chung J. et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
10	<input checked="" type="checkbox"/>	US 2005000	2005010	32	Reactor for producing rea	118/715	257/E21.2		Lee, Chung J. et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
11	<input checked="" type="checkbox"/>	US 2004026	2004123	24	Low temperature epitaxia	117/2	257/E21.1		Tsong, Ignatius S.T.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
12	<input checked="" type="checkbox"/>	US 2004025	2004122	31	Reactor for producing rea	118/722	118/715;		Lee, Chung J. et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
13	<input checked="" type="checkbox"/>	US 2004024	2004120	7	Ultraviolet (UV) and plas	427/62	505/430		Selvamanickam, Ve	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
14	<input checked="" type="checkbox"/>	US 2004024	2004120	21	Thin metal oxide filn and	438/608	438/104;		Fukuhisa, Koji et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
15	<input checked="" type="checkbox"/>	US 2004024	2004120	21	Mechanical enhancer add	428/447	257/E21.2		Vincent, Jean Louis	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
16	<input checked="" type="checkbox"/>	US 2004014	2004072	19	Semiconductor processin	156/345.3			Satoh, Kiyoshi et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>

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L8	6	(thin adj film and first adj reactant and first adj energy and second adj energy first adj chemisorbed).clm.	US-PGPU B	OR	ON	2005/10/28 13:37